AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

1-33 (Cancelled)

34. (Currently Amended) The electronic structure having embedded substantially flush circuit features, according to Claim ~~32~~ 42, wherein said first dielectric layer comprises:

a reinforcing material selected from the group consisting of glass fibers and glass fabric.

35. (Cancelled)

36. (Currently Amended) The electronic structure having embedded substantially flush circuit features, according to Claim ~~32~~ 42, wherein said ~~circuitry layer is~~ circuit lines are up to about 20 microns thick.

37. (Currently Amended) The electronic structure having embedded substantially flush circuit features, according to Claim ~~33~~ 42, wherein said conductive material comprises copper.

38. (Currently Amended) The electronic structure having embedded substantially flush circuit features, according to Claim ~~32~~ 42, wherein said ~~circuitry layer is~~ circuit lines are about 5 to about 20 microns thick.

39. (Currently Amended) The electronic structure having embedded substantially flush circuit features, according to Claim ~~32~~ 42, wherein said ~~circuitry layer is~~ circuit lines are about 5 to about 10 microns thick.

40. (Currently Amended) The electronic structure having embedded substantially flush circuit features, according to Claim ~~33~~ 42, wherein said seed layer comprises copper or chromium.

41. (Currently Amended) The electronic structure having embedded substantially flush circuit features, according to Claim ~~33~~ 42, wherein said seed layer is about 100 angstroms to about 5000 angstroms thick.

42. (New) An electronic structure having embedded substantially flush circuit features comprising:

a first dielectric layer of polymeric material having a first top surface:

a second dielectric layer of polymeric material on said first top surface of said first dielectric layer of polymeric material, having a second top surface, said second layer of polymeric material also having trench features therein, having a bottom and sidewalls;

a conductive seed layer located on said bottom and sidewalls;

and electrically conductive material deposited in said trench features forming electrically conductive circuit lines being substantially flush with said second top surface of said second dielectric layer of polymeric material, wherein said polymeric material is at least one member selected from the group consisting of thermoplastic resin and thermosetting resin,

and further including a third dielectric layer of polymeric material located on said electrically conductive circuit lines, wherein the second dielectric layer of polymeric material is a different material than said first and third dielectric layer of polymeric material.

43. (New) The electronic structure of claim 42 wherein said electrically conductive material is plated metal.

44. (New) The electronic structure of claim 42 wherein the circuit lines are about 0.5 to about 1 mil wide, about 0.5 to about 2 mils apart and up to about 20 microns thick.

45. (New) An electronic structure which comprises at least two of the structures of claim 42 stacked together.

46. (New) The electronic structure of claim 42 wherein said trench features are formed by laser oblation.